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Amendments to the Abstract:

Please insert as new page 20 the following abstract (taken from applicants' PCT International Patent Application) as amended:

Abstract

The invention relates to a method for microstructuring electronic components, which yields high resolutions (≤ 200 nm) at a good aspect ratio while being significantly less expensive than photolithographic methods. The inventive method comprises the following steps: i) a planar unhardened sol film of a nanocomposite composition according to claim 1 is produced; ii) a target substrate consisting of a bottom coat (b) and a support (c) is produced; iii) sol film material obtained in step i) is applied to the bottom coat (b) obtained in step ii) by means of a microstructured transfer embossing stamp; iv) the applied sol film material is hardened; v) the transfer embossing stamp is separated, whereby an embossed microstructure is obtained as a top coat (a). The method for producing a microstructured semiconductor material comprises the following additional steps: vi) the remaining layer of the nanocomposite sol film is plasma etched, preferably with CHF_3/O_2 plasma; vii) the bottom coat is plasma etched, preferably with O_2 plasma; viii) the semiconductor material is etched or the semiconductor material is doped in the etched areas.